2-input NAND gate

Rev. 1 — 16 September 2013

**Product data sheet** 

### 1. General description

The 74HC1G00-Q100; 74HCT1G00-Q100 is a single 2-input NAND gate. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

### 2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
   Specified from -40 °C to +85 °C and from -40 °C to +125 °C
- Wide supply voltage range from 2.0 V to 6.0 V
- Input levels:
  - For 74HC1G00-Q100: CMOS level
  - For 74HCT1G00-Q100: TTL level
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

### 3. Ordering information

#### Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74HC1G00GW-Q100	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads;	SOT353-1				
74HCT1G00GW-Q100			body width 1.25 mm					
74HC1G00GV-Q100	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753				
74HCT1G00GV-Q100								



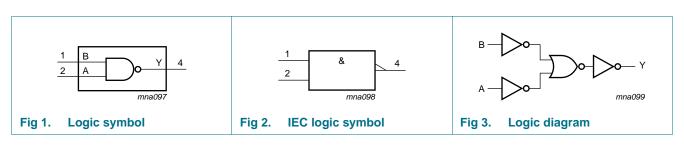
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### 4. Marking

Table 2.   Marking codes	
Type number	Marking <sup>[1]</sup>
74HC1G00GW-Q100	НА
74HCT1G00GW-Q100	ТА
74HC1G00GV-Q100	H00
74HCT1G00GV-Q100	Т00

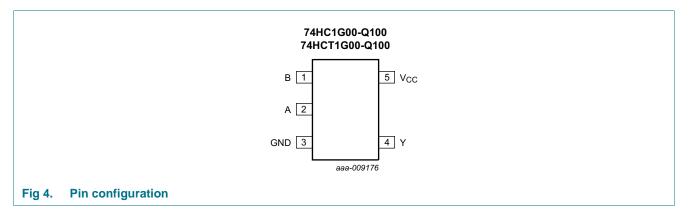
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

### 5. Functional diagram



### 6. Pinning information

### 6.1 Pinning



#### 6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
В	1	data input
А	2	data input
GND	3	ground (0 V)
Y	4	data output
V <sub>CC</sub>	5	supply voltage

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## 7. Functional description

#### Table 4.Function table

*H* = *HIGH* voltage level; *L* = *LOW* voltage level

Input		Output
Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V). [1]

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_{\rm I}$ < -0.5 V or $V_{\rm I}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
I <sub>OK</sub>	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	-	±20	mA
Ι <sub>Ο</sub>	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±12.5	mA
I <sub>CC</sub>	supply current		-	25	mA
I <sub>GND</sub>	ground current		-25	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \ ^{\circ}C$ to +125 $^{\circ}C$	[2] _	200	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] Above 55 °C, the value of  $P_{tot}$  derates linearly with 2.5 mW/K.

### 9. Recommended operating conditions

#### Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC1	74HC1G00-Q100			74HCT1G00-Q100		
			Min	Тур	Max	Min	Тур	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	$V_{CC}$	0	-	V <sub>CC</sub>	V
Vo	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	-	139	-	-	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

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## **10. Static characteristics**

#### Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb}$  = 25 °C.

Symbol	Parameter	Conditions	-40	–40 °C to +85 °C			–40 °C to +125 °C	
			Min	Тур	Max	Min	Max	
For type	74HC1G00-Q100							
V <sub>IH</sub>	HIGH-level input	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	V
	voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	V
	voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V
V <sub>он</sub>	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	V
		$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V
		$I_0 = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	V
		$I_{O} = -2.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
		$I_{O}$ = -2.6 mA; $V_{CC}$ = 6.0 V	5.63	5.81	-	5.2	-	V
V <sub>OL</sub>	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$						
		$I_0 = 20 \ \mu A; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		$I_{O}$ = 2.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
		$I_0 = 2.6 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
l <sub>l</sub>	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	1.0	-	1.0	μA
lcc	supply current	$V_I = V_{CC} \text{ or GND}; I_O = 0 \text{ A};$ $V_{CC} = 6.0 \text{ V}$	-	-	10	-	20	μA
CI	input capacitance		-	· 1.5	-	-	-	pF
For type	74HCT1G00-Q100							
V <sub>IH</sub>	HIGH-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
VIL	LOW-level input voltage	$V_{CC}$ = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V <sub>OH</sub>	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	4.4	4.5	-	4.4	-	V
		$I_{O}$ = -2.0 mA; $V_{CC}$ = 4.5 V	4.13	4.32	-	3.7	-	V
√ <sub>OL</sub>	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_0 = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_{O}$ = 2.0 mA; $V_{CC}$ = 4.5 V	-	0.15	0.33	-	0.4	V
l	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	1.0	-	1.0	μA

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Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C	Unit	
			Min	Тур	Max	Min	Max	
I <sub>CC</sub>	supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$ A; $V_{CC} = 5.5$ V	-	-	10	-	20	μA
$\Delta I_{CC}$	additional supply current	per input; $V_{CC} = 4.5 \text{ V}$ to 5.5 V; $V_I = V_{CC} - 2.1 \text{ V}$ ; $I_O = 0 \text{ A}$	-	-	500	-	850	μΑ
CI	input capacitance			1.5	-	-	-	pF

#### Table 7. Static characteristics ...continued

### **11. Dynamic characteristics**

#### Table 8. Dynamic characteristics

GND = 0 V;  $t_r = t_f \le 6.0$  ns; All typical values are measured at  $T_{amb} = 25$  °C. For test circuit, see Figure 6

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C	Unit	
			-	Min	Тур	Max	Min	Max	
For type	74HC1G00-Q100		'			1	l	1	
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	[1]						
		$V_{CC} = 2.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	25	115	-	135	ns
		$V_{CC} = 4.5 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	9	23	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	7	-	-	-	ns
		$V_{CC} = 6.0 \text{ V}; \text{ C}_{L} = 50 \text{ pF}$		-	8	20	-	23	ns
C <sub>PD</sub>	power dissipation capacitance	$V_I = GND$ to $V_{CC}$	[2]	-	19	-	-	-	pF
For type	74HCT1G00-Q100								
t <sub>pd</sub>	propagation delay	A and B to Y; see Figure 5	<u>[1]</u>						
		$V_{CC}$ = 4.5 V; $C_{L}$ = 50 pF		-	12	24	-	27	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	10	-	-	-	ns
$C_{PD}$	power dissipation capacitance	$V_{I}$ = GND to $V_{CC}$ – 1.5 V	[2]	-	21	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $~~C_{PD}$  is used to determine the dynamic power dissipation P  $_{D}$  (µW).

 $P_{D}$  =  $C_{PD} \times V_{CC}{}^{2} \times f_{i}$  +  $\sum$  ( $C_{L} \times V_{CC}{}^{2} \times f_{o}$ ) where:

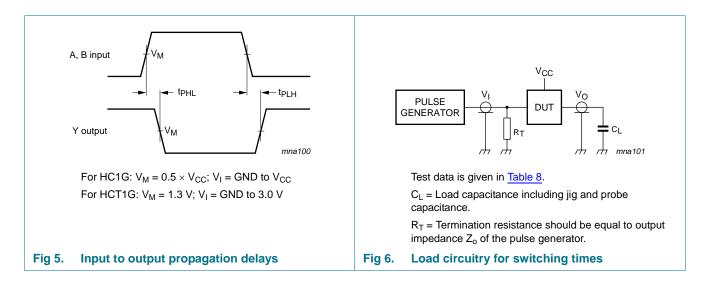
 $f_i$  = input frequency in MHz;  $f_o$  = output frequency in MHz

 $C_L$  = output load capacitance in pF  $V_{CC}$  = supply voltage in Volts

 $\Sigma (C_L \times V_{CC}^2 \times f_0) = \text{sum of outputs}$ 

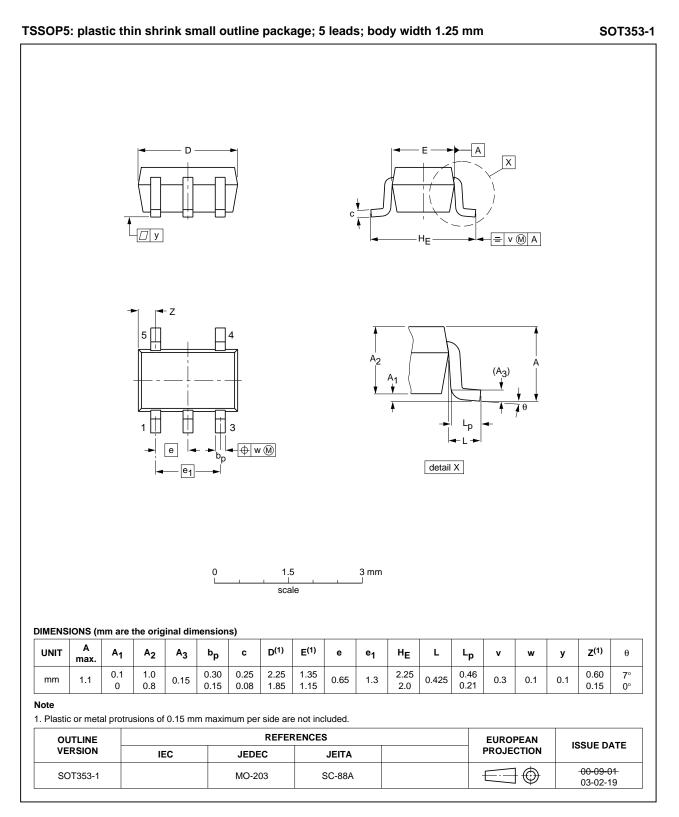
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## 12. Waveforms



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### 13. Package outline

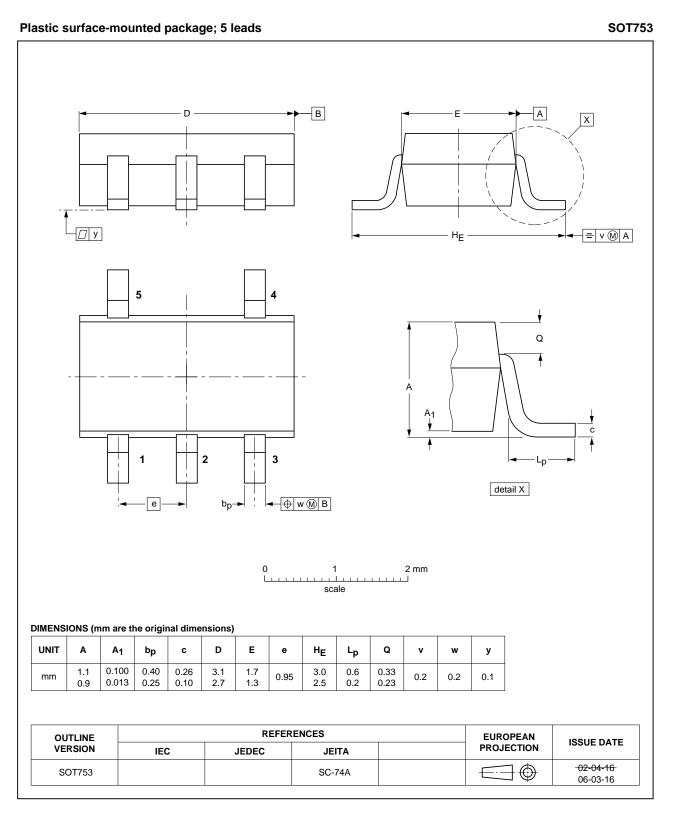


#### Fig 7. Package outline SOT353-1 (TSSOP5)

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#### Fig 8. Package outline SOT753 (SC-74A)

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## 14. Abbreviations

Table 9.	Abbreviations				
Acronym	Description				
CMOS	Complementary Metal Oxide Semiconductor				
DUT	Device Under Test				
ESD	ElectroStatic Discharge				
HBM	Human Body Model				
MIL	Military				
MM	Machine Model				
TTL	Transistor-Transistor Logic				

## **15. Revision history**

Table 10. Revision history	0. Revision history							
Document ID	Release date	Data sheet status	Change notice	Supersedes				
74HC_HCT1G00_Q100 v.1	20130916	Product data sheet	-	-				

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
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